VS-HFA16TA60CSPbF

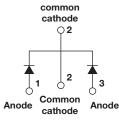
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HEXFRED[®] Ultrafast Soft Recovery Diode, 2 x 8 A



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Base



PRODUCT SUMMARY								
Package	TO-263AB (D ² PAK)							
I _{F(AV)}	2 x 8 A							
V _R	600 V							
V _F at I _F	1.4 V							
t _{rr} typ.	18 ns							
T _J max.	150 °C							
Diode variation	Common cathode							

FEATURES

- Ultrafast and ultrasoft recovery
- Very low I_{RRM} and Q_{rr}
- Specified at operating conditions
- Meets MSL level 1, per J-STD-020, LF maximum peak of 260 °C
- AEC-Q101 qualified
- Material categorization: for definitions of compliance please see <u>www.vishay.com/doc?99912</u>

BENEFITS

- Reduced RFI and EMI
- · Reduced power loss in diode and switching transistor
- Higher frequency operation
- Reduced snubbing
- Reduced parts count

DESCRIPTION

VS-HFA16TA60CS is a state of the art center tap ultrafast recovery diode. Employing the latest in epitaxial construction and advanced processing techniques it features a superb combination of characteristics which result in performance which is unsurpassed by any rectifier previously available. With basic ratings of 600 V and 8 A per leg continuous current, the VS-HFA16TA60CS is especially well suited for use as the companion diode for IGBTs and MOSFETs. In addition to ultrafast recovery time, the HEXFRED® product line features extremely low values of peak recovery current (I_{RRM}) and does not exhibit any tendency to "snap-off" during the tb portion of recovery. The HEXFRED features combine to offer designers a rectifier with lower noise and significantly lower switching losses in both the diode and the switching transistor. These HEXFRED advantages can help to significantly reduce snubbing, component count and heatsink sizes. The HEXFRED VS-HFA16TA60CS is ideally suited for applications in power supplies and power conversion systems (such as inverters), motor drives, and many other similar applications where high speed, high efficiency is needed.

ABSOLUTE MAXIMUM RATINGS									
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS					
Cathode to anode voltage	V _R		600	V					
Maximum continuous forward current per leg	1_	T _C = 100 °C	8						
per device	IF	1 _C = 100 0	16	А					
Single pulse forward current	I _{FSM}		60	~					
Maximum repetitive forward current	I _{FRM}		24						
Maximum power dissipation	PD	T _C = 25 °C	36	W					
Maximum power dissipation	FD	T _C = 100 °C	14	vv					
Operating junction and storage temperature range	T _J , T _{Stg}		-55 to +150	°C					

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ELECTRICAL SPECIFICATIONS PER LEG (T_J = 25 °C unless otherwise specified)									
PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNITS		
Cathode to anode breakdown voltage	V _{BR}	I _R = 100 μA	600	-	-				
Maximum forward voltage	V _{FM}	I _F = 8.0 A		-	1.4	1.7	V		
		I _F = 16 A	See fig. 1	-	1.7	2.1			
		$I_F = 8.0 \text{ A}, T_J = 125 \text{ °C}$		-	1.4	1.7			
Maximum reverse	I _{RM}	$V_R = V_R$ rated	Coo fig. 0	-	0.3	5.0	μA		
leakage current		T_J = 125 °C, V_R = 0.8 x V_R rated	See fig. 2	-	100	500			
Junction capacitance	CT	V _R = 200 V See fig. 3		-	10	25	pF		
Series inductance	L _S	Measured lead to lead 5 mm from pa	ackage body	-	8.0	-	nH		

DYNAMIC RECOVERY CHARACTERISTICS PER LEG ($T_J = 25$ °C unless otherwise specified)									
PARAMETER	SYMBOL	TEST CO	NDITIONS	MIN.	TYP.	MAX.	UNITS		
	t _{rr}	I _F = 1.0 A, dI _F /dt = 200	A/ μ s, V _R = 30 V	-	18	-	ns		
Reverse recovery time See fig. 5, 6 and 16	t _{rr1}	T _J = 25 °C	I _F = 8.0 A dI _F /dt = 200 A/μs V _R = 200 V	-	37	55			
	t _{rr2}	T _J = 125 °C		-	55	90			
Peak recovery current	I _{RRM1}	T _J = 25 °C		-	3.5	5.0	- A nC A/μs		
See fig. 7 and 8	I _{RRM2}	T _J = 125 °C		-	4.5	8.0			
Reverse recovery charge	Q _{rr1}	T _J = 25 °C		-	65	138			
See fig. 9 and 10	Q _{rr2}	T _J = 125 °C		-	124	360			
Peak rate of fall of recovery current during t _b See fig. 11 & 12	dl _{(rec)M} /dt1	T _J = 25 °C		-	240	-			
	dl _{(rec)M} /dt2	T _J = 125 °C		-	210	-			

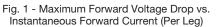
THERMAL - MECHANICAL SPECIFICATIONS										
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS				
Lead temperature	T _{lead}	0.063" from case (1.6 mm) for 10 s	-	-	300	°C				
Junction to case, single leg conducting			-	-	3.5					
Junction to case, both legs conducting	– R _{thJC}		-	-	1.75	K/W				
Thermal resistance, junction to ambient	R _{thJA}	Typical socket mount	-	-	80					
Weight			-	2	-	g				
Weight			-	0.07	-	oz.				
Mounting torque			6.0 (5.0)	-	12 (10)	kgf · cm (lbf · in)				
Marking device		Case style TO-263AB (D ² PAK)	HFA16TA60CS							

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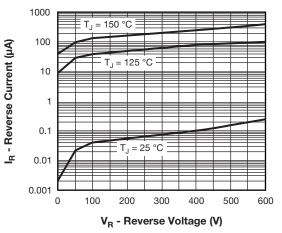


100 I_F - Instantaneous Forward Current (A) 10 150 °C = 125 °C T_ T₁ = 25 °C 1 0.1 0.4 0.8 1.2 1.6 2.0 2.4 2.8 3.2 V_{FM} - Forward Voltage Drop (V)



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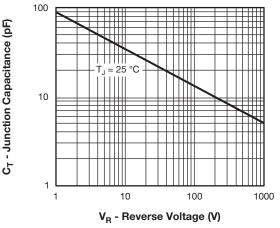


Fig. 3 - Typical Junction Capacitance vs. Reverse Voltage (Per Leg)

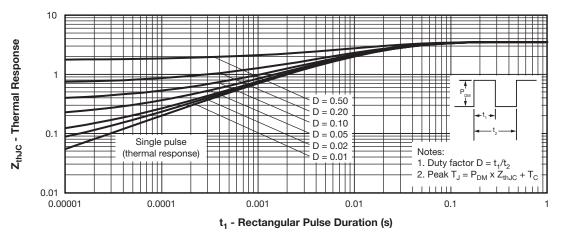


Fig. 4 - Maximum Thermal Impedance Z_{thJC} Characteristics (Per Leg)



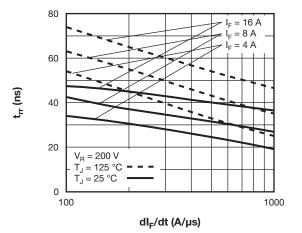


Fig. 5 - Typical Reverse Recovery Time vs. dl_F/dt (Per Leg)

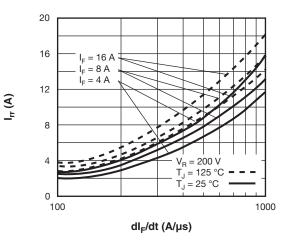


Fig. 6 - Typical Recovery Current vs. dl_F/dt (Per Leg)

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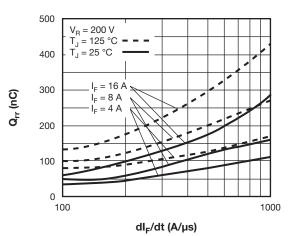


Fig. 7 - Typical Stored Charge vs. dl_F/dt (Per Leg)

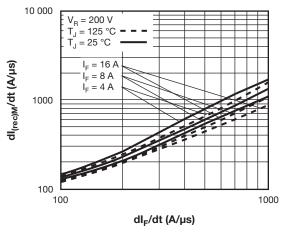


Fig. 8 - Typical dl_{(rec)M}/dt vs. dl_F/dt (Per Leg)

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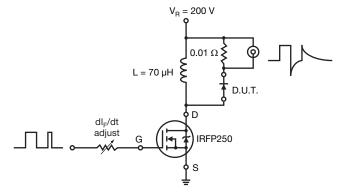
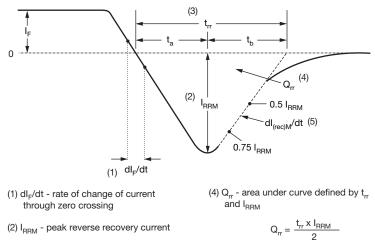


Fig. 9 - Reverse Recovery Parameter Test Circuit



- (3) $t_{\rm rr}$ reverse recovery time measured from zero crossing point of negative going ${\rm I_F}$ to point where a line passing through 0.75 ${\rm I_{RRM}}$ and 0.50 ${\rm I_{RRM}}$ extrapolated to zero current.
- (5) dI_{(rec)M}/dt peak rate of change of current during $\rm t_b$ portion of $\rm t_{rr}$
- Fig. 10 Reverse Recovery Waveform and Definitions

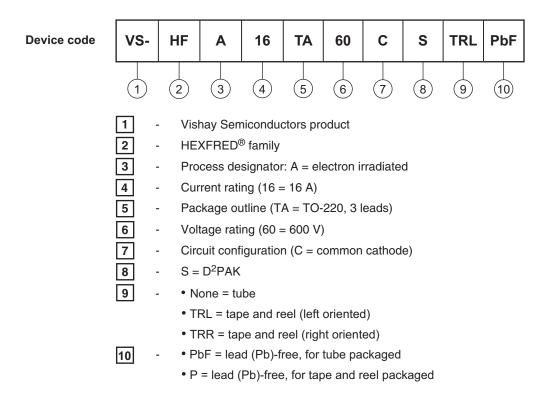


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ORDERING INFORMATION TABLE

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LINKS TO RELATED DOCUMENTS							
Dimensions	www.vishay.com/doc?95046						
Part marking information	www.vishay.com/doc?95054						
Packaging information	www.vishay.com/doc?95032						
SPICE model	www.vishay.com/doc?95689						

ORDERING INFORMATION (Example)									
PREFERRED P/N	QUANTITY PER TUBE	MINIMUM ORDER QUANTITY	PACKAGING DESCRIPTION						
VS-HFA16TA60CSPBF	50	1000	Antistatic plastic tube						
VS-HFA16TA60CSTRRP	800	800	13" diameter reel						
VS-HFA16TA60CSTRLP	800	800	13" diameter reel						

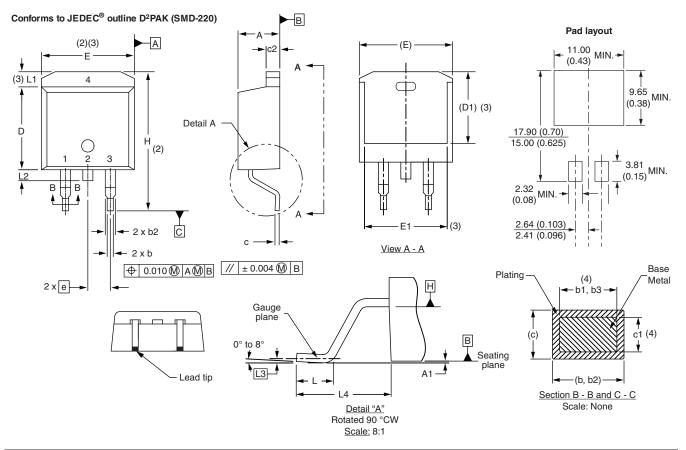
Outline Dimensions



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D²PAK

DIMENSIONS in millimeters and inches



SYMBOL	MILLIMETERS		INCHES		NOTES	ES NOTES		SYMBOL	MILLIN	ETERS	INC	HES	NOTES
STMBOL	MIN.	MAX.	MIN.	MAX.	NOTES	NOTES	STINDUL	MIN.	MAX.	MIN.	MAX.	NOTES	
A	4.06	4.83	0.160	0.190			D1	6.86	8.00	0.270	0.315	3	
A1	0.00	0.254	0.000	0.010			E	9.65	10.67	0.380	0.420	2, 3	
b	0.51	0.99	0.020	0.039			E1	7.90	8.80	0.311	0.346	3	
b1	0.51	0.89	0.020	0.035	4		е	2.54	BSC	0.100	0.100 BSC		
b2	1.14	1.78	0.045	0.070			Н	14.61	15.88	0.575	0.625		
b3	1.14	1.73	0.045	0.068	4		L	1.78	2.79	0.070	0.110		
С	0.38	0.74	0.015	0.029			L1	-	1.65	-	0.066	3	
c1	0.38	0.58	0.015	0.023	4		L2	1.27	1.78	0.050	0.070		
c2	1.14	1.65	0.045	0.065			L3	0.25	BSC	0.010) BSC		
D	8.51	9.65	0.335	0.380	2		L4	4.78	5.28	0.188	0.208		

Notes

⁽¹⁾ Dimensioning and tolerancing per ASME Y14.5 M-1994

(2) Dimension D and E do not include mold flash. Mold flash shall not exceed 0.127 mm (0.005") per side. These dimensions are measured at the outmost extremes of the plastic body

⁽³⁾ Thermal pad contour optional within dimension E, L1, D1 and E1

⁽⁴⁾ Dimension b1 and c1 apply to base metal only

⁽⁵⁾ Datum A and B to be determined at datum plane H

⁽⁶⁾ Controlling dimension: inch

⁽⁷⁾ Outline conforms to JEDEC[®] outline TO-263AB

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